

## 2SC4901

### Silicon NPN Epitaxial

REJ03G0733-0300  
 (Previous ADE-208-1127A)  
 Rev.3.00  
 Aug.10.2005

### Application

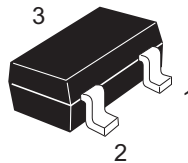
UHF / VHF wide band amplifier

### Features

- High gain bandwidth product  
 $f_T = 9$  GHz Typ
- High gain, low noise figure  
 $PG = 13.0$  dB Typ,  $NF = 1.2$  dB Typ at  $f = 900$  MHz

### Outline

RENESAS Package code: PTSP0003ZA-A  
 (Package name: CMPAK<sup>®</sup>)



1. Emitter
2. Base
3. Collector

Note: Marking is "YK-".

\*CMPAK is a trademark of Renesas Technology Corp.

### Absolute Maximum Ratings

( $T_a = 25^\circ\text{C}$ )

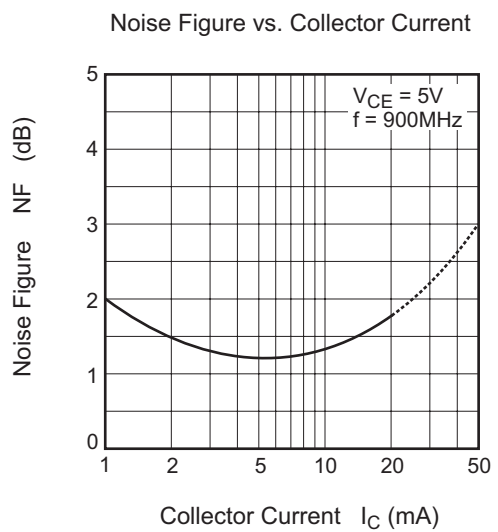
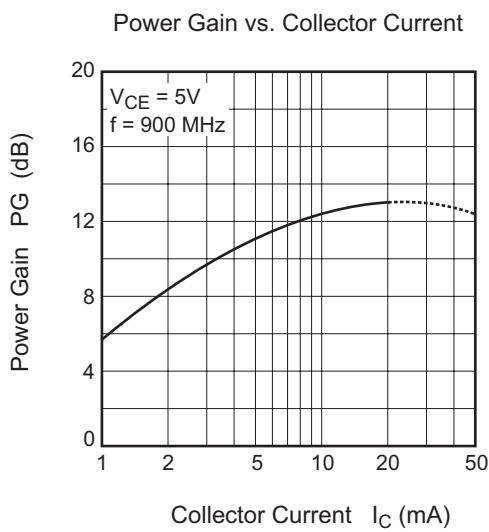
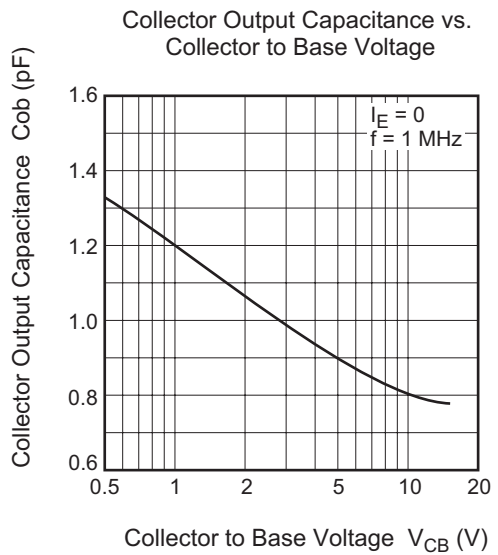
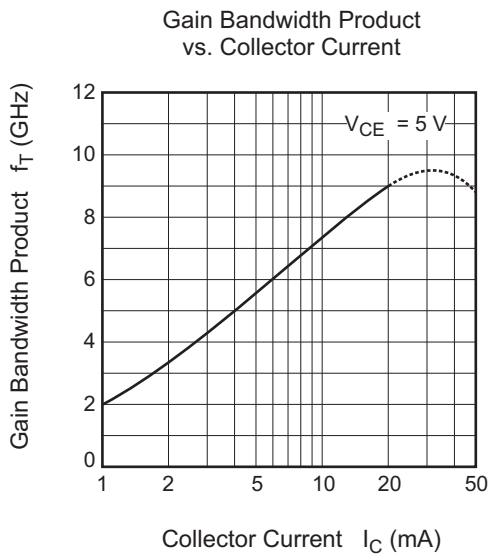
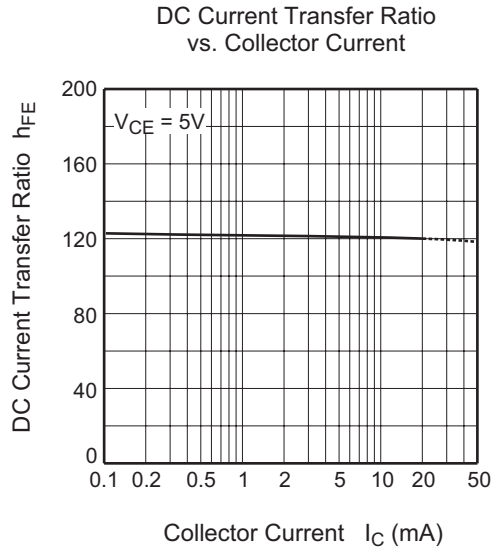
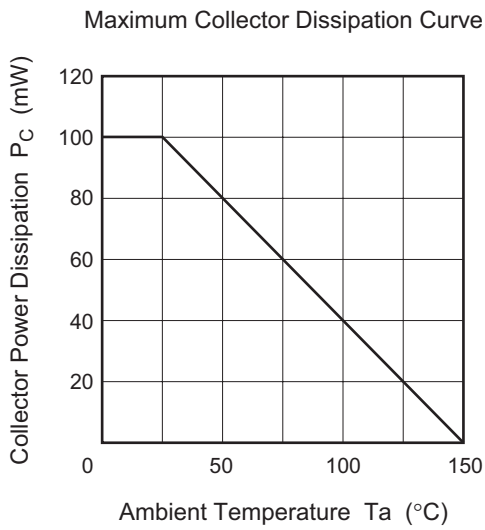
Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	15	V
Collector to emitter voltage	$V_{CEO}$	9	V
Emitter to base voltage	$V_{EBO}$	1.5	V
Collector current	$I_C$	50	mA
Collector power dissipation	$P_C$	100	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

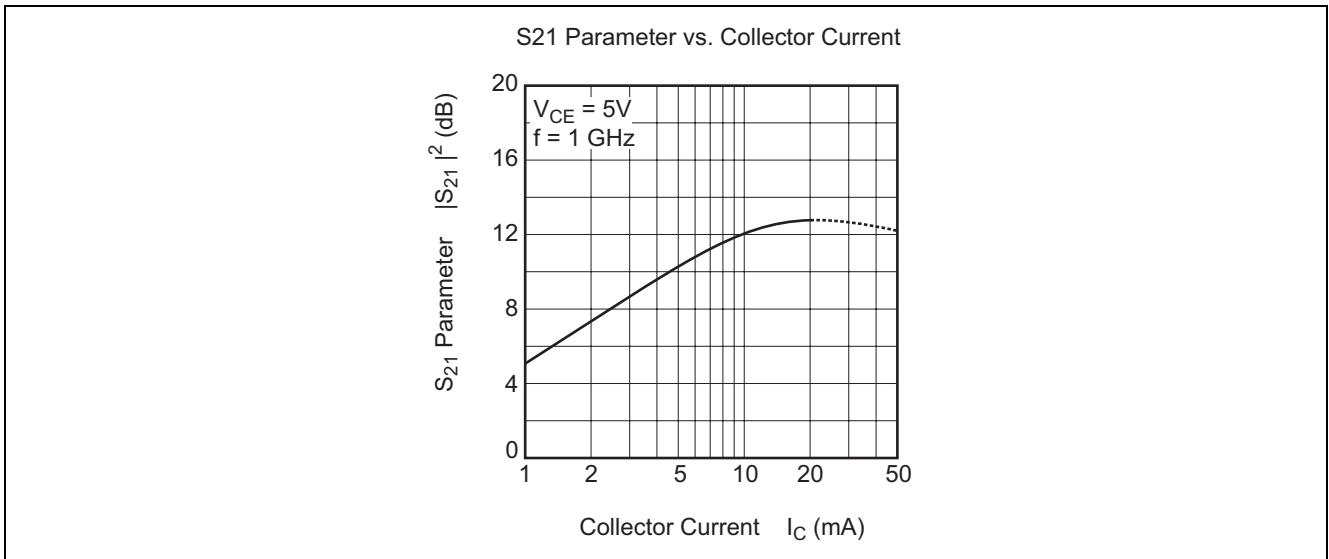
## Electrical Characteristics

(Ta = 25°C)

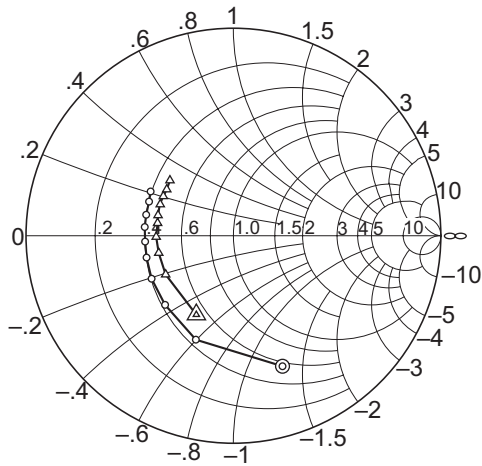
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	15	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector cutoff current	$I_{CBO}$	—	—	10	$\mu A$	$V_{CB} = 12 V, I_E = 0$
	$I_{CEO}$	—	—	1	mA	$V_{CE} = 9 V, R_{BE} = \infty$
Emitter cutoff current	$I_{EBO}$	—	—	10	$\mu A$	$V_{EB} = 1.5 V, I_C = 0$
DC current transfer ratio	$h_{FE}$	50	120	250		$V_{CE} = 5 V, I_C = 20 mA$
Collector output capacitance	$C_{ob}$	—	0.9	1.4	pF	$V_{CB} = 5 V, I_E = 0, f = 1 MHz$
Gain bandwidth product	$f_T$	6.0	9.0	—	GHz	$V_{CE} = 5 V, I_C = 20 mA$
Power gain	PG	10.0	13.0	—	dB	$V_{CE} = 5 V, I_C = 20 mA,$ $f = 900 MHz$
Noise figure	NF	—	1.2	2.5	dB	$V_{CE} = 5 V, I_C = 5 mA,$ $f = 900 MHz$

Main Characteristics



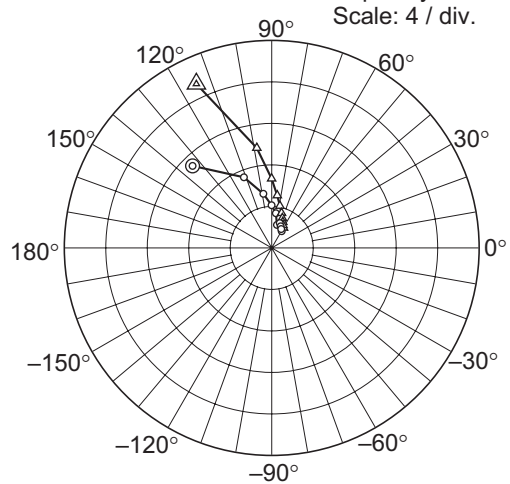


S11 Parameter vs. Frequency



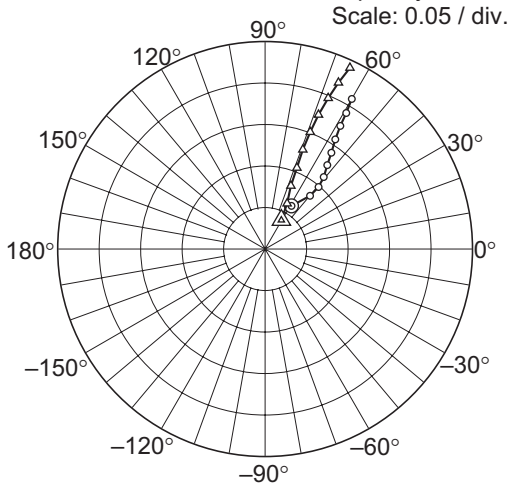
Condition:  $V_{CE} = 5\text{ V}$ ,  $Z_o = 50\ \Omega$   
 200 to 2000 MHz (200 MHz step)  
 ○ (  $I_C = 5\text{ mA}$  )  
 △ (  $I_C = 20\text{ mA}$  )

S21 Parameter vs. Frequency



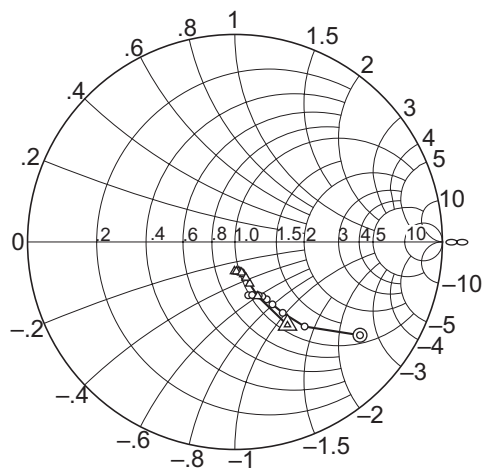
Condition:  $V_{CE} = 5\text{ V}$ ,  $Z_o = 50\ \Omega$   
 200 to 2000 MHz (200 MHz step)  
 ○ (  $I_C = 5\text{ mA}$  )  
 △ (  $I_C = 20\text{ mA}$  )

S12 Parameter vs. Frequency



Condition:  $V_{CE} = 5\text{ V}$ ,  $Z_o = 50\ \Omega$   
 200 to 2000 MHz (200 MHz step)  
 ○ (  $I_C = 5\text{ mA}$  )  
 △ (  $I_C = 20\text{ mA}$  )

S22 Parameter vs. Frequency



Condition:  $V_{CE} = 5\text{ V}$ ,  $Z_o = 50\ \Omega$   
 200 to 2000 MHz (200 MHz step)  
 ○ (  $I_C = 5\text{ mA}$  )  
 △ (  $I_C = 20\text{ mA}$  )

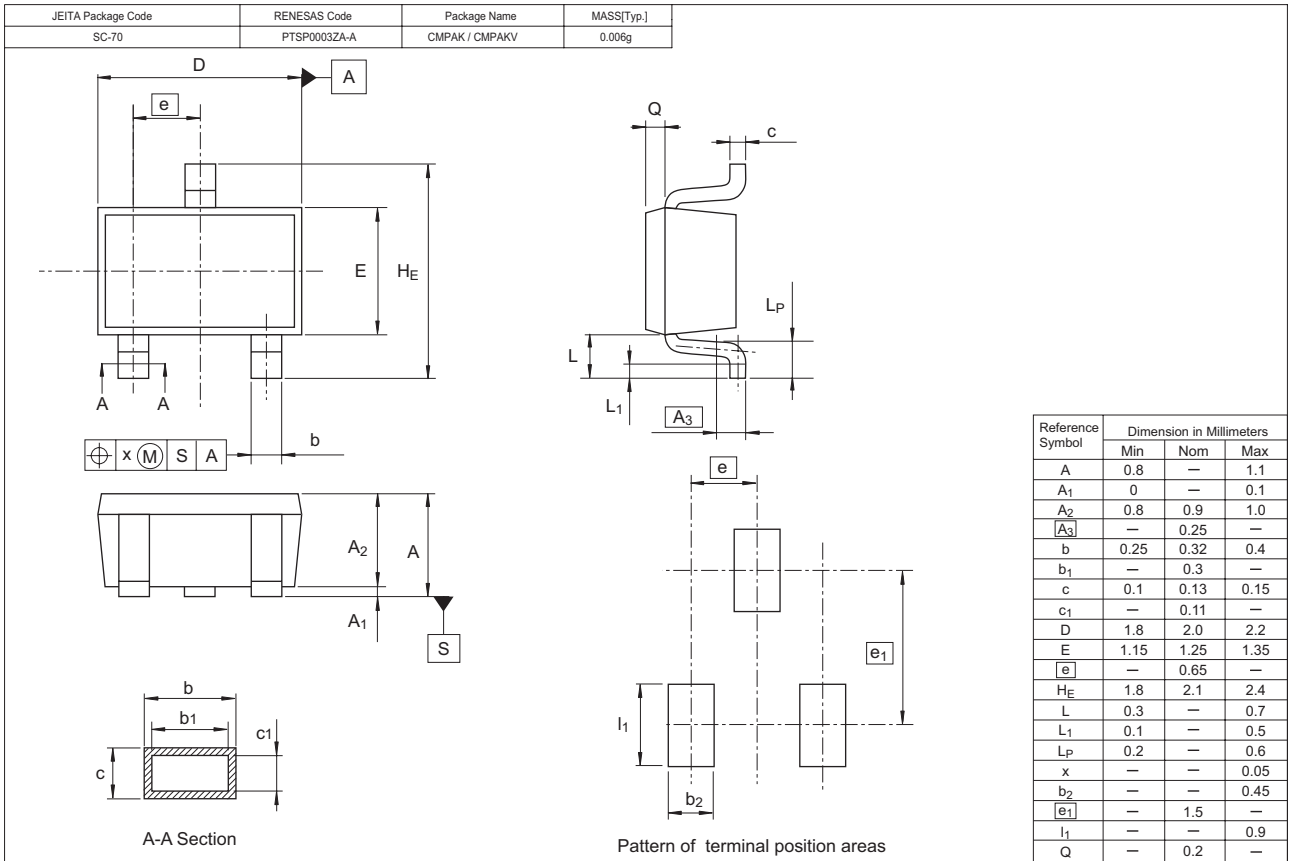
**S Parameter** $(V_{CE} = 5\text{ V}, I_C = 5\text{ mA}, Z_O = 50\ \Omega, \text{Emitter common})$ 

Freq. (MHz)	S11		S21		S12		S22	
	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
200	0.672	-69.4	10.99	134.0	0.0610	58.8	0.752	-26.7
400	0.533	-109.9	7.32	111.5	0.0841	49.9	0.528	-50.5
600	0.469	-134.7	5.28	98.8	0.0989	49.3	0.412	-56.0
800	0.446	-152.3	4.12	90.2	0.112	50.9	0.351	-59.0
1000	0.432	-165.9	3.37	83.2	0.126	53.5	0.316	-61.0
1200	0.427	-176.2	2.88	77.2	0.141	55.5	0.294	-63.3
1400	0.430	174.1	2.52	72.1	0.157	57.4	0.282	-66.0
1600	0.433	166.5	2.26	67.5	0.174	58.6	0.274	-69.1
1800	0.439	158.0	2.04	63.3	0.191	59.2	0.269	-72.0
2000	0.453	151.9	1.88	59.2	0.209	60.0	0.265	-76.0

**S Parameter** $(V_{CE} = 5\text{ V}, I_C = 20\text{ mA}, Z_O = 50\ \Omega, \text{Emitter common})$ 

Freq. (MHz)	S11		S21		S12		S22	
	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
200	0.421	-115.2	17.40	114.7	0.0399	50.6	0.474	-57.7
400	0.377	-150.2	9.74	98.5	0.0609	64.2	0.284	-67.2
600	0.370	-167.0	6.68	90.1	0.0822	67.8	0.213	-70.5
800	0.373	-179.1	5.09	84.0	0.105	68.6	0.180	-72.9
1000	0.371	170.6	4.13	79.0	0.128	69.2	0.161	-74.9
1200	0.377	164.9	3.49	74.3	0.151	68.9	0.151	-77.6
1400	0.384	156.9	3.04	70.3	0.174	68.3	0.146	-80.7
1600	0.388	150.7	2.71	66.8	0.197	67.3	0.143	-83.5
1800	0.392	145.3	2.45	63.3	0.219	66.2	0.142	-87.2
2000	0.406	139.0	2.25	59.5	0.241	64.9	0.141	-91.0

### Package Dimensions



### Ordering Information

Part Name	Quantity	Shipping Container
2SC4901YK-TL-E	3000	φ 178 mm Reel, 8 mm Emboss Taping

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